



## P-Channel 1.8-V (G-S) MOSFET

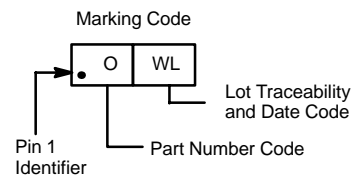
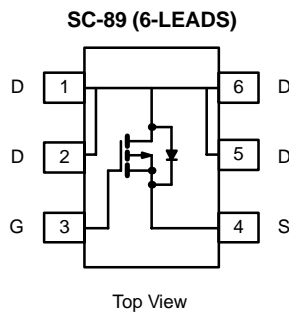
PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
-12	0.165 @ $V_{GS} = -4.5$ V	-0.95
	0.220 @ $V_{GS} = -2.5$ V	-0.82
	0.280 @ $V_{GS} = -1.8$ V	-0.67

### FEATURES

- TrenchFET® Power MOSFET
- Low Threshold
- Smallest LITTLE FOOT® Package: 1.6 mm x 1.6 mm
- Low 0.6-mm Profile

### APPLICATIONS

- Cell Phones and Pagers
  - Load Switch



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	-12		V	
Gate-Source Voltage	$V_{GS}$	$\pm 8$			
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$I_D$	$T_A = 25^\circ\text{C}$	-0.95	-0.87	A
		$T_A = 70^\circ\text{C}$	-0.76	-0.69	
Pulsed Drain Current	$I_{DM}$	-4			
Continuous Diode Current (Diode Conduction) <sup>a</sup>	$I_S$	-0.18	-0.14		
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25^\circ\text{C}$	0.21	0.17	W
		$T_A = 70^\circ\text{C}$	0.13	0.10	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 5$ sec	500	600	$^\circ\text{C/W}$
		Steady State	600	720	

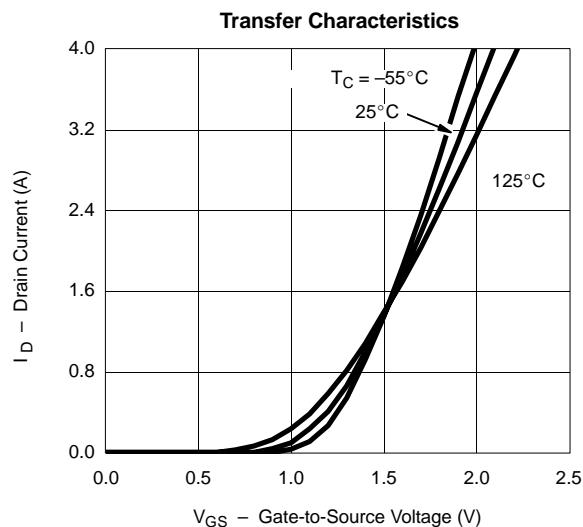
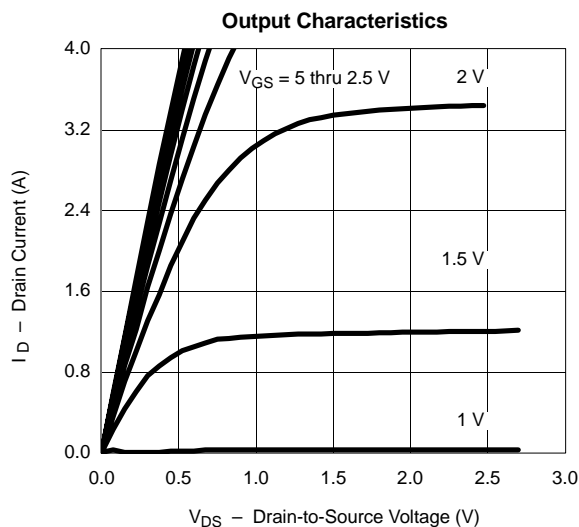
Notes  
a. Surface Mounted on 1" x 1" FR4 Board with minimum copper.

**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.45			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -9.6 V, V <sub>GS</sub> = 0 V			-1	μA
		V <sub>DS</sub> = -9.6 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			-5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = -5 V, V <sub>GS</sub> = -4.5 V	-4			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -0.87 A		0.140	0.165	Ω
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -0.75 A		0.180	0.220	
		V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -0.2 A		0.230	0.280	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -0.87 A		3.5		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = -0.14 A, V <sub>GS</sub> = 0 V		-0.78	-1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -6 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -0.87 A		3.8	6	nC
Gate-Source Charge	Q <sub>gs</sub>			0.7		
Gate-Drain Charge	Q <sub>gd</sub>			0.8		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -6 V, R <sub>L</sub> = 12 Ω I <sub>D</sub> ≅ -0.5 A, V <sub>GEN</sub> = -4.5 V, R <sub>G</sub> = 6 Ω		15	30	ns
Rise Time	t <sub>r</sub>			20	40	
Turn-Off Delay Time	t <sub>d(off)</sub>			30	60	
Fall Time	t <sub>f</sub>			16	30	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>		I <sub>F</sub> = -0.14 A, di/dt = 100 A/μs		20	

## Notes

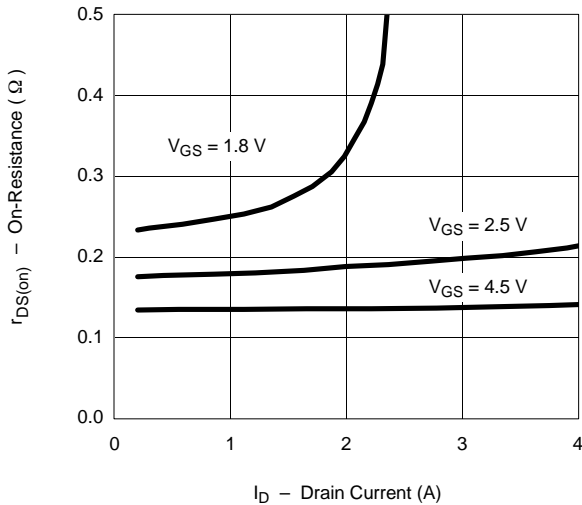
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.  
b. Guaranteed by design, not subject to production testing.

**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

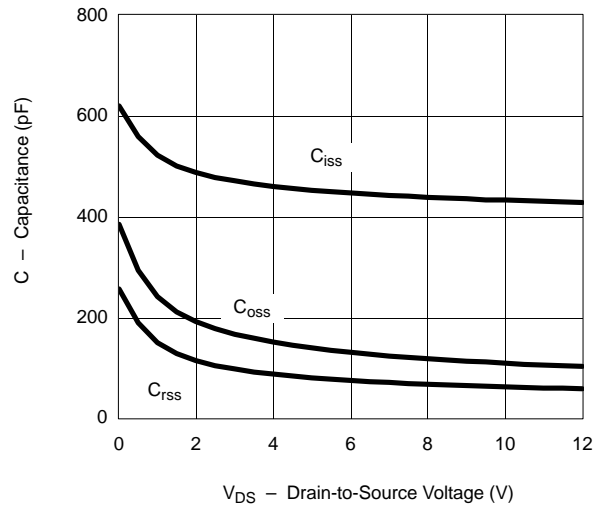


**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

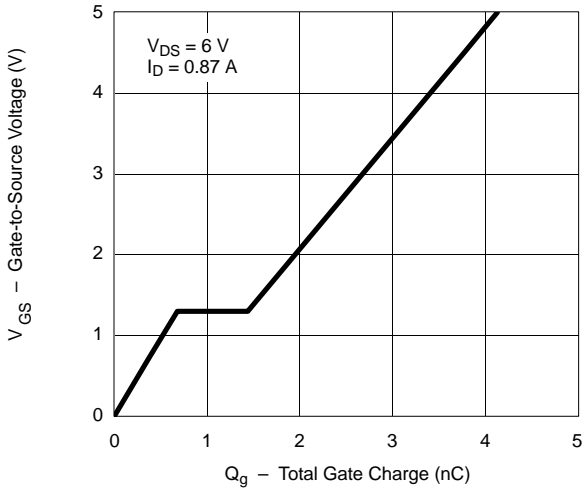
On-Resistance vs. Drain Current



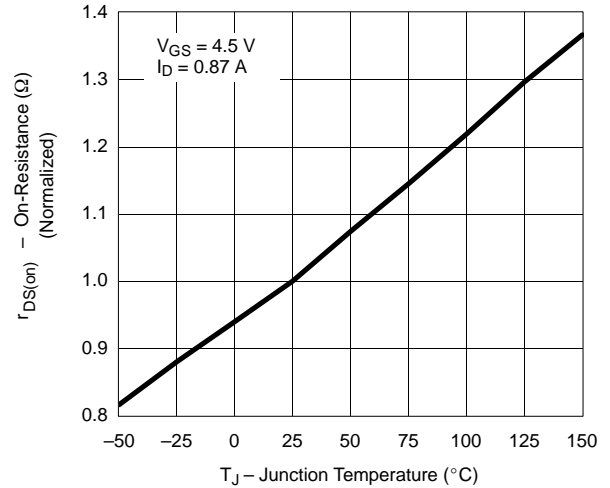
Capacitance



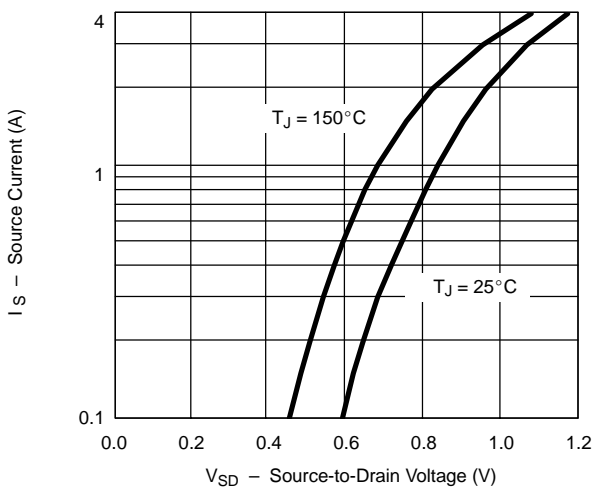
Gate Charge



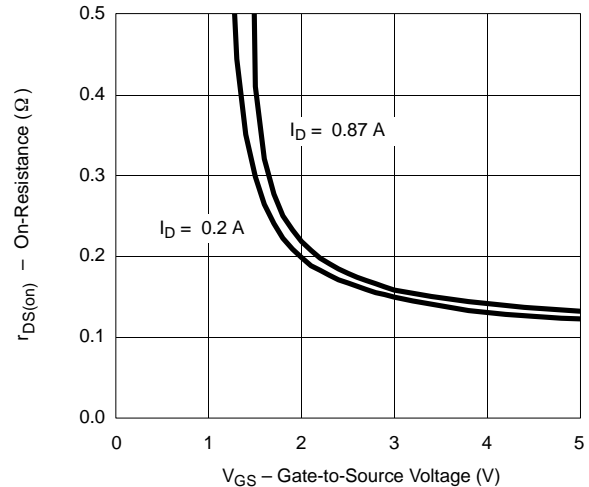
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

